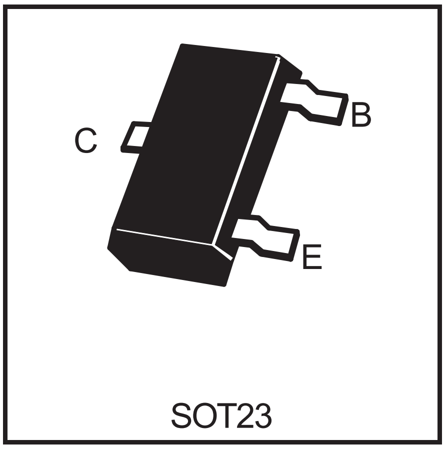
SOT23 NPN SILICON PLANAR SMALL SIGNAL TRANSISTOR

ISSUE 2 – MARCH 1995

FMMTA43

PARTMARKING DETAIL – FMMTA43 – 1E



SOT23

ABSOLUTE MAXIMUM RATINGS.

PARAMETER	SYMBOL	VALUE	UNIT
Collector-Emitter Voltage	V_{CEO}	200	V
Emitter-Base Voltage	V_{EBO}	5	V
Continuous Collector Current	I_C	100	mA
Power Dissipation at T_{amb}=25°C	P_{tot}	200	mW
Operating and Storage Temperature Range	T_j:T_{stg}	-55 to +150	°C

ELECTRICAL CHARACTERISTICS (at Tamb= 25°C).

PARAMETER	SYMBOL	MIN.	MAX.	UNIT	CONDITIONS.
Collector-Base Breakdown Voltage	$V_{(BR)CBO}$	200		V	I_C=1mA, I_E=0
Emitter-Base Breakdown Voltage	$V_{(BR)EBO}$	5		V	I_E=100mA, I_C=0
Collector Cut-Off Current	I_{CBO}		0.1	μA	V_{CB}=30V, I_E=0
Static Forward Current Transfer Ratio	h_{FE}	40	400		I_C=5mA, V_{CE}=10V*
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$		0.25	V	I_C=10mA,I_B=1mA
Transition Frequency	f_T	50		MHz	I_C=5mA, V_{CE}=10V
Output Capacitance	C_{obo}		4	pF	V_{CB}=10V, f=140kHz, I_E=0

*Measured under pulsed conditions. Pulse width=300 μs. Duty cycle ≤2%

Spice parameter data is available upon request for this device